

# 74ALVC245

Octal bus transceiver; 3-state

Rev. 02 — 7 January 2008

Product data sheet

## 1. General description

The 74ALVC245 is an octal transceiver featuring non-inverting 3-state bus compatible outputs in both send and receive directions. The 74ALVC245 features an output enable input ( $\overline{OE}$ ) for easy cascading and send/receive input (DIR) for direction control.  $\overline{OE}$  controls the outputs, so that the buses are effectively isolated.

## 2. Features

- Wide supply voltage range from 1.65 V to 3.6 V
- Complies with JEDEC standard:
  - ◆ JESD8-7 (1.65 V to 1.95 V)
  - ◆ JESD8-5 (2.3 V to 2.5 V)
  - ◆ JESD8B/JESD36 (2.7 V to 3.6 V)
- 3.6 V tolerant inputs/outputs
- CMOS low-power consumption
- Direct interface with TTL levels (2.7 V to 3.6 V)
- Power-down mode
- Latch-up performance exceeds 250 mA
- ESD protection:
  - ◆ HBM JESD22-A114E exceeds 2000 V
  - ◆ MM JESD22-A115-A exceeds 200 V

## 3. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
74ALVC245D	-40 °C to +85 °C	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1
74ALVC245PW	-40 °C to +85 °C	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1
74ALVC245BQ	-40 °C to +85 °C	DHVQFN20	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body 2.5 × 4.5 × 0.85 mm	SOT764-1

4. Functional diagram

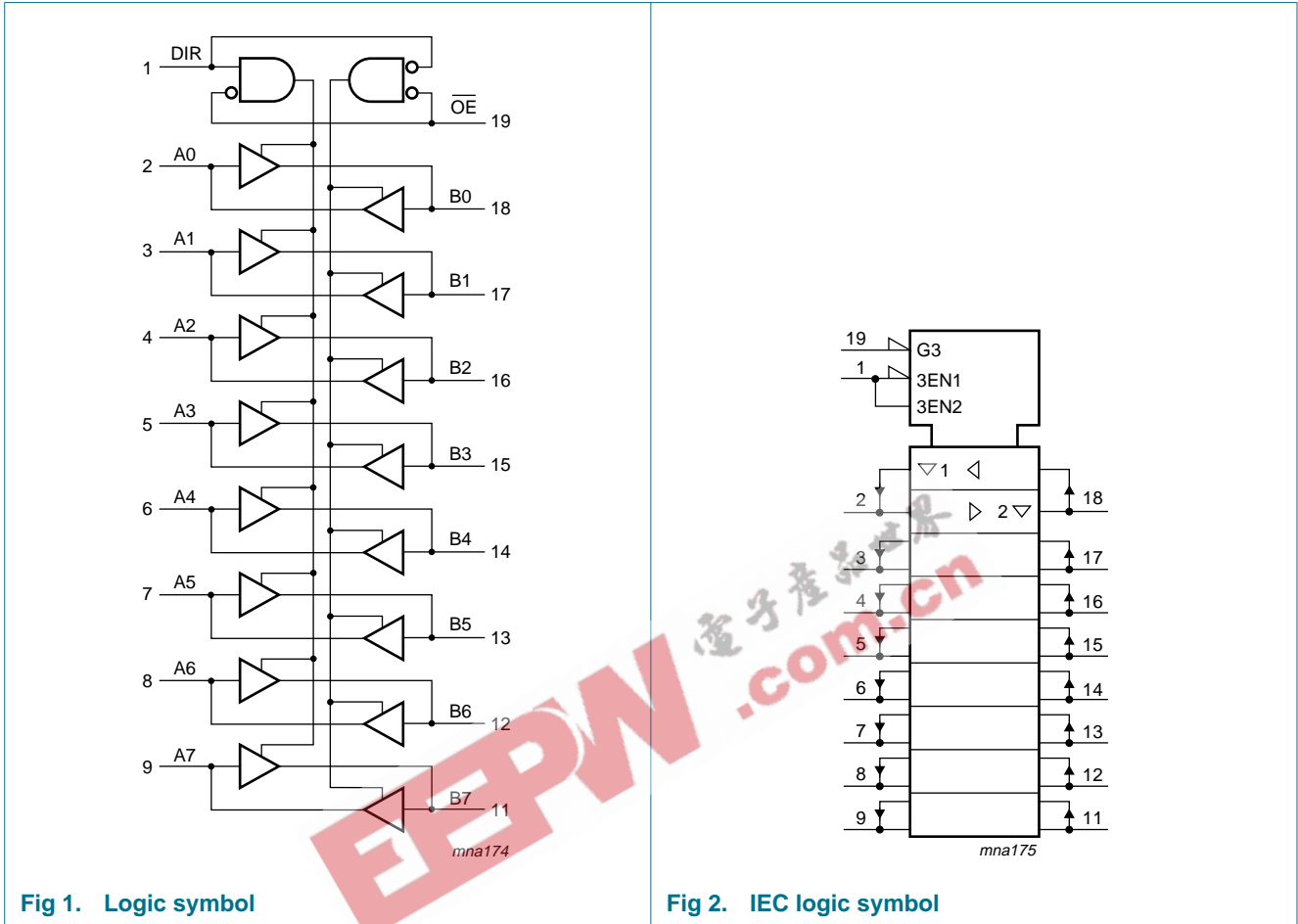
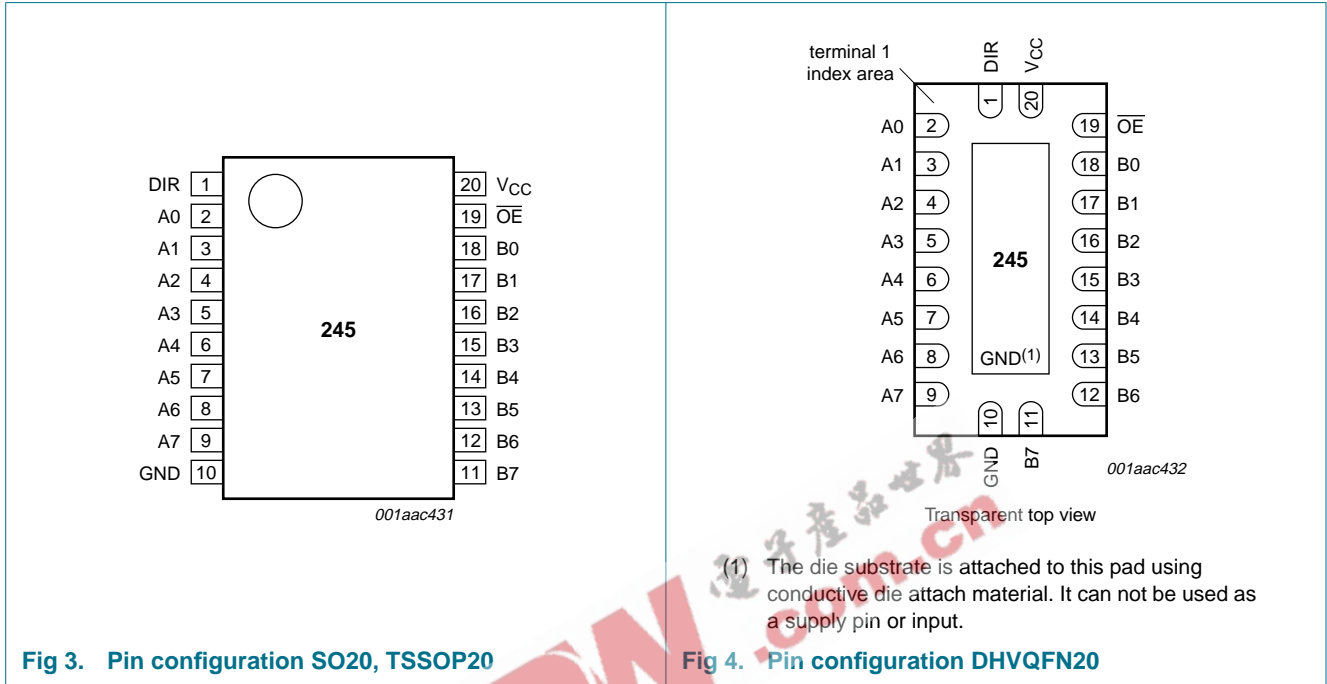


Fig 1. Logic symbol

Fig 2. IEC logic symbol

## 5. Pinning information

### 5.1 Pinning



### 5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
DIR	1	direction control
A[0:7]	2, 3, 4, 5, 6, 7, 8, 9	data input/output
B[0:7]	18, 17, 16, 15, 14, 13, 12, 11	data input/output
GND	10	ground (0 V)
OE	19	output enable input (active LOW)
V <sub>CC</sub>	20	supply voltage

## 6. Functional description

Table 3. Function table<sup>[1]</sup>

Input		Input/output	
OE	DIR	An	Bn
L	L	A = B	input
L	H	input	B = A
H	X	Z	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

## 7. Limiting values

**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+4.6	V
$V_I$	input voltage		-0.5	+4.6	V
$I_{IK}$	input clamping current	$V_I < 0$ V	[1] -50	-	mA
$I_{OK}$	output clamping current	$V_O > V_{CC}$ or $V_O < 0$ V	-	±50	mA
$V_O$	output voltage	output HIGH or LOW state	[2] -0.5	$V_{CC} + 0.5$	V
		output 3-state	[2] -0.5	+4.6	V
		power-down mode, $V_{CC} = 0$ V	[3] -0.5	+4.6	V
$I_O$	output current	$V_O = 0$ V to $V_{CC}$	-	±50	mA
$I_{CC}$	supply current		-	100	mA
$I_{GND}$	ground current		-100	-	mA
$T_{stg}$	storage temperature		-65	+150	°C
$P_{tot}$	total power dissipation	$T_{amb} = -40$ °C to +85 °C			
		SO20 package	[4] -	500	mW
		TSSOP20 package	[5] -	500	mW
		DHVQFN20 package	[6] -	500	mW

- [1] The minimum input voltage ratings may be exceeded if the input current ratings are observed.
- [2] The output voltage ratings may be exceeded if the output current ratings are observed.
- [3] When  $V_{CC} = 0$  V (Power-down mode), the output voltage can be 3.6 V in normal operation.
- [4]  $P_{tot}$  derates linearly with 8 mW/K above 70 °C.
- [5]  $P_{tot}$  derates linearly with 5.5 mW/K above 60 °C.
- [6]  $P_{tot}$  derates linearly with 4.5 mW/K above 60 °C.

## 8. Recommended operating conditions

**Table 5. Recommended operating conditions**

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		1.65	3.6	V
$V_I$	input voltage		0	3.6	V
$V_O$	output voltage	output HIGH or LOW state	0	$V_{CC}$	V
		output 3-state	0	3.6	V
		power-down mode, $V_{CC} = 0$ V	0	3.6	V
$T_{amb}$	ambient temperature		-40	+85	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 1.65$ V to 2.7 V	-	20	ns/V
		$V_{CC} = 2.7$ V to 3.6 V	-	10	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C			Unit
			Min	Typ <sup>[1]</sup>	Max	
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	0.65 × V <sub>CC</sub>	-	-	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.7	-	-	V
		V <sub>CC</sub> = 2.7 V to 3.6 V	2.0	-	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	-	-	0.35 × V <sub>CC</sub>	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	V
		V <sub>CC</sub> = 2.7 V to 3.6 V	-	-	0.8	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = 100 μA; V <sub>CC</sub> = 1.65 V to 3.6 V	V <sub>CC</sub> - 0.2	-	-	V
		I <sub>O</sub> = 6 mA; V <sub>CC</sub> = 1.65 V	1.25	-	-	V
		I <sub>O</sub> = 12 mA; V <sub>CC</sub> = 2.3 V	1.8	-	-	V
		I <sub>O</sub> = 18 mA; V <sub>CC</sub> = 2.3 V	1.7	-	-	V
		I <sub>O</sub> = 12 mA; V <sub>CC</sub> = 2.7 V	2.2	-	-	V
		I <sub>O</sub> = 18 mA; V <sub>CC</sub> = 3.0 V	2.4	-	-	V
		I <sub>O</sub> = 24 mA; V <sub>CC</sub> = 3.0 V	2.2	-	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = -100 μA; V <sub>CC</sub> = 1.65 V to 3.6 V	-	-	0.2	V
		I <sub>O</sub> = -6 mA; V <sub>CC</sub> = 1.65 V	-	-	0.3	V
		I <sub>O</sub> = -12 mA; V <sub>CC</sub> = 2.3 V	-	-	0.4	V
		I <sub>O</sub> = -18 mA; V <sub>CC</sub> = 2.3 V	-	-	0.6	V
		I <sub>O</sub> = -12 mA; V <sub>CC</sub> = 2.7 V	-	-	0.4	V
		I <sub>O</sub> = -18 mA; V <sub>CC</sub> = 3.0 V	-	-	0.4	V
		I <sub>O</sub> = -24 mA; V <sub>CC</sub> = 3.0 V	-	-	0.55	V
I <sub>OZ</sub>	OFF-state output current	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> ; V <sub>O</sub> = V <sub>CC</sub> or GND; V <sub>CC</sub> = 3.6 V	[2]	±0.1	±10.0	μA
I <sub>I</sub>	input leakage current	V <sub>I</sub> = V <sub>CC</sub> or GND; V <sub>CC</sub> = 3.6 V	-	±0.1	±5.0	μA
I <sub>OFF</sub>	power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V	-	±0.1	±10.0	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = V <sub>CC</sub> or GND; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 3.6 V	-	0.2	10	μA
ΔI <sub>CC</sub>	additional supply current	per input pin; V <sub>CC</sub> = 3.0 V to 3.6 V; V <sub>I</sub> = V <sub>CC</sub> - 0.6 V; I <sub>O</sub> = 0 A;	-	5	750	μA
C <sub>I</sub>	input capacitance		-	3.5	-	pF
C <sub>I/O</sub>	input/output capacitance		-	3.5	-	pF

[1] All typical values are measured at V<sub>CC</sub> = 3.3 V and T<sub>amb</sub> = 25 °C.

[2] For transceivers, the parameter I<sub>OZ</sub> includes the input leakage current.

## 10. Dynamic characteristics

**Table 7. Dynamic characteristics**

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 7](#).

Symbol	Parameter	Conditions	-40 °C to +85 °C			Unit
			Min	Typ <sup>[1]</sup>	Max	
t <sub>pd</sub>	propagation delay	An to Bn; Bn to An; see <a href="#">Figure 5</a> <sup>[2]</sup>				
		V <sub>CC</sub> = 1.65 V to 1.95 V	1.0	2.7	6.0	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.0	2.1	3.5	ns
		V <sub>CC</sub> = 2.7 V	1.0	3.0	3.6	ns
t <sub>en</sub>	enable time	$\overline{OE}$ to An; $\overline{OE}$ to Bn; see <a href="#">Figure 6</a> <sup>[2]</sup>				
		V <sub>CC</sub> = 1.65 V to 1.95 V	1.0	4.0	8.6	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.0	3.0	6.0	ns
		V <sub>CC</sub> = 2.7 V	1.0	2.6	6.3	ns
t <sub>dis</sub>	disable time	$\overline{OE}$ to An; $\overline{OE}$ to Bn; see <a href="#">Figure 6</a> <sup>[2]</sup>				
		V <sub>CC</sub> = 1.65 V to 1.95 V	1.0	4.4	8.0	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.0	2.3	4.8	ns
		V <sub>CC</sub> = 2.7 V	1.0	3.3	5.3	ns
C <sub>PD</sub>	power dissipation capacitance	per buffer; V <sub>I</sub> = GND to V <sub>CC</sub> ; V <sub>CC</sub> = 3.3 V <sup>[3]</sup>				
		outputs enabled	-	25	-	pF
		outputs disabled	-	1	-	pF

[1] All typical values are measured at T<sub>amb</sub> = 25 °C and V<sub>CC</sub> = 1.8 V, 2.5 V, 2.7 V and 3.3 V.

[2] t<sub>pd</sub> is the same as t<sub>PLH</sub> and t<sub>PHL</sub>.

t<sub>en</sub> is the same as t<sub>PZL</sub> and t<sub>PZH</sub>.

t<sub>dis</sub> is the same as t<sub>PLZ</sub> and t<sub>PHZ</sub>.

[3] C<sub>PD</sub> is used to determine the dynamic power dissipation (P<sub>D</sub> in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$  where:

f<sub>i</sub> = input frequency in MHz;

f<sub>o</sub> = output frequency in MHz;

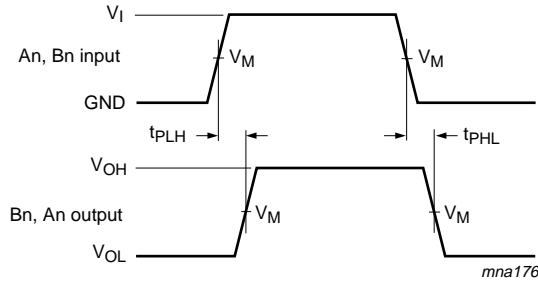
C<sub>L</sub> = output load capacitance in pF;

V<sub>CC</sub> = supply voltage in V;

N = number of inputs switching;

Σ(C<sub>L</sub> × V<sub>CC</sub><sup>2</sup> × f<sub>o</sub>) = sum of the outputs.

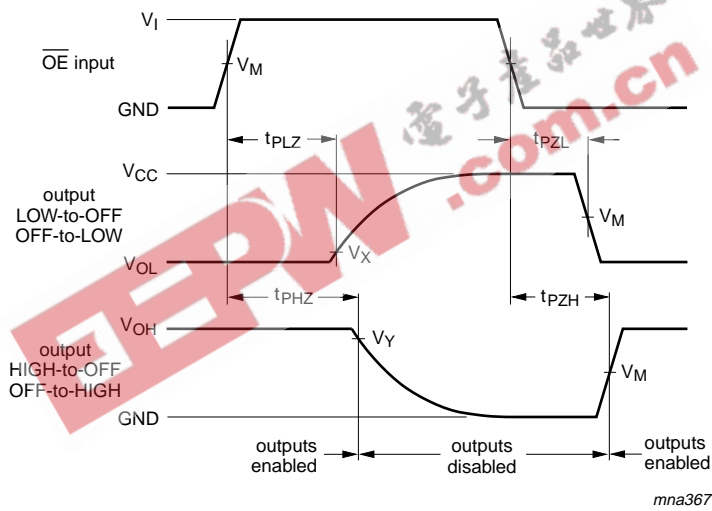
11. Waveforms



Measurement points are given in [Table 8](#).

$V_{OL}$  and  $V_{OH}$  are typical voltage output levels that occur with the output load.

Fig 5. Propagation delay input (An, Bn) to output (Bn, An)



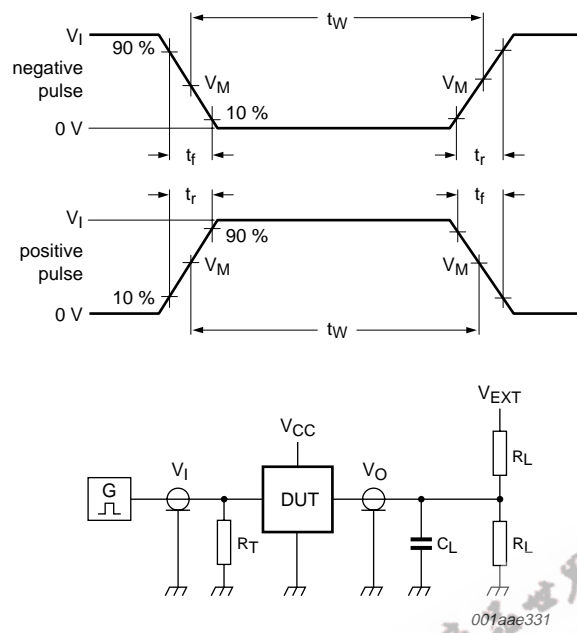
Measurement points are given in [Table 8](#).

$V_{OL}$  and  $V_{OH}$  are typical voltage output levels that occur with the output load.

Fig 6. Enable and disable times

Table 8. Measurement points

Supply voltage	Input		Output		
$V_{CC}$	$V_I$	$V_M$	$V_M$	$V_X$	$V_Y$
1.65 V to 1.95 V	$V_{CC}$	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	$V_{OL} + 0.15 \text{ V}$	$V_{OH} - 0.15 \text{ V}$
2.3 V to 2.7 V	$V_{CC}$	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	$V_{OL} + 0.15 \text{ V}$	$V_{OH} - 0.15 \text{ V}$
2.7 V	2.7 V	1.5 V	1.5 V	$V_{OL} + 0.3 \text{ V}$	$V_{OH} - 0.3 \text{ V}$
3.0 V to 3.6 V	2.7 V	1.5 V	1.5 V	$V_{OL} + 0.3 \text{ V}$	$V_{OH} - 0.3 \text{ V}$



Test data is given in [Table 9](#).

Definitions test circuit:

$R_T$  = Termination resistance should be equal to output impedance  $Z_o$  of the pulse generator

$C_L$  = Load capacitance including jig and probe capacitance

$R_L$  = Load resistor

Fig 7. Load circuitry for switching times

Table 9. Test data

Supply voltage	Input		Load		$V_{EXT}$		
$V_{CC}$	$V_I$	$t_r, t_f$	$C_L$	$R_L$	$t_{PLH}, t_{PHL}$	$t_{PLZ}, t_{PZL}$	$t_{PHZ}, t_{PZH}$
1.65 V to 1.95 V	$V_{CC}$	$\leq 2.0$ ns	30 pF	1 k $\Omega$	open	$2 \times V_{CC}$	GND
2.3 V to 2.7 V	$V_{CC}$	$\leq 2.0$ ns	30 pF	500 $\Omega$	open	$2 \times V_{CC}$	GND
2.7 V	2.7 V	$\leq 2.5$ ns	50 pF	500 $\Omega$	open	6 V	GND
3.0 V to 3.6 V	2.7 V	$\leq 2.5$ ns	50 pF	500 $\Omega$	open	6 V	GND



12. Package outline

SO20: plastic small outline package; 20 leads; body width 7.5 mm

SOT163-1

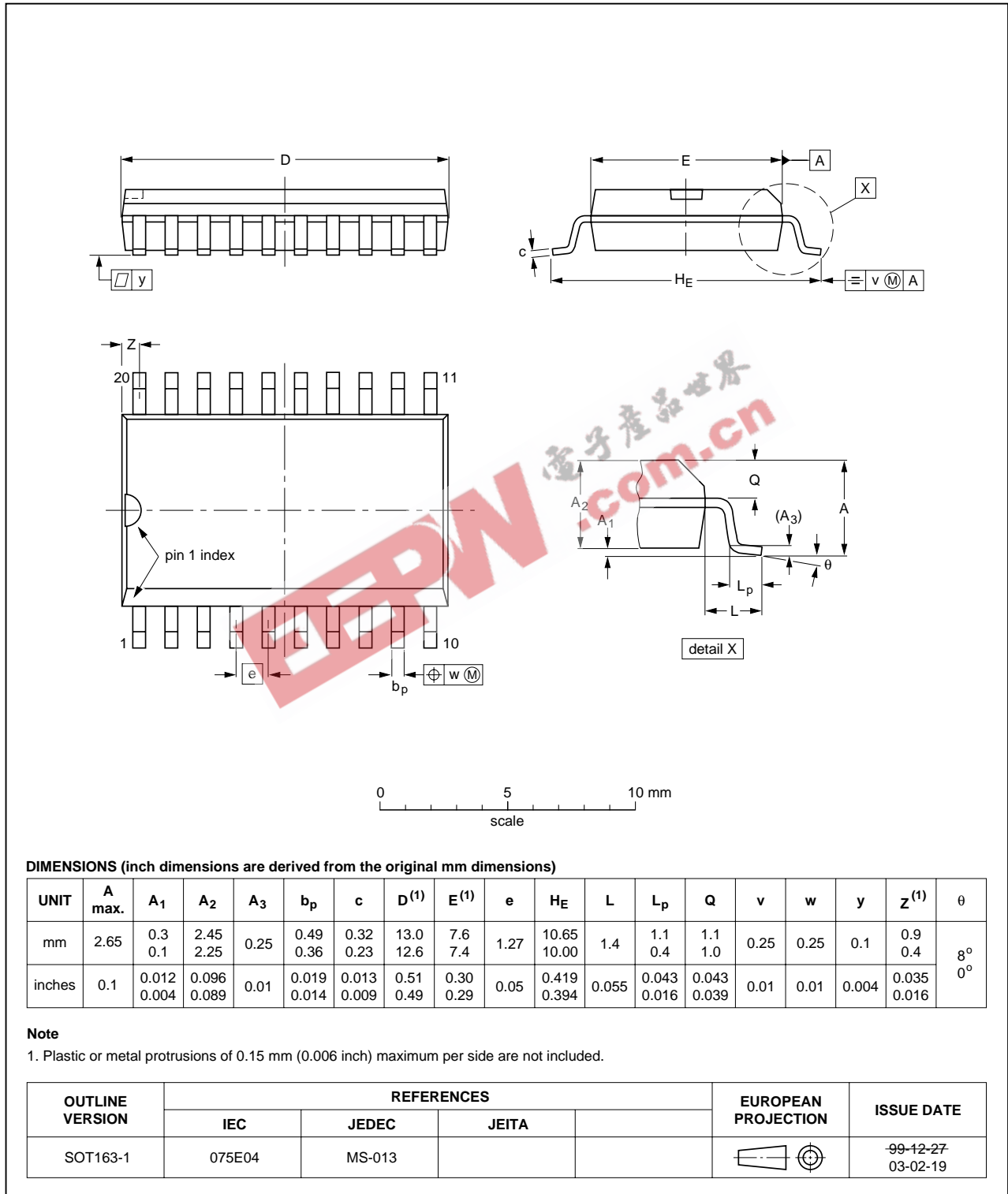


Fig 8. Package outline SOT163-1 (SO20)

TSSOP20: plastic thin shrink small outline package; 20 leads; body width 4.4 mm

SOT360-1

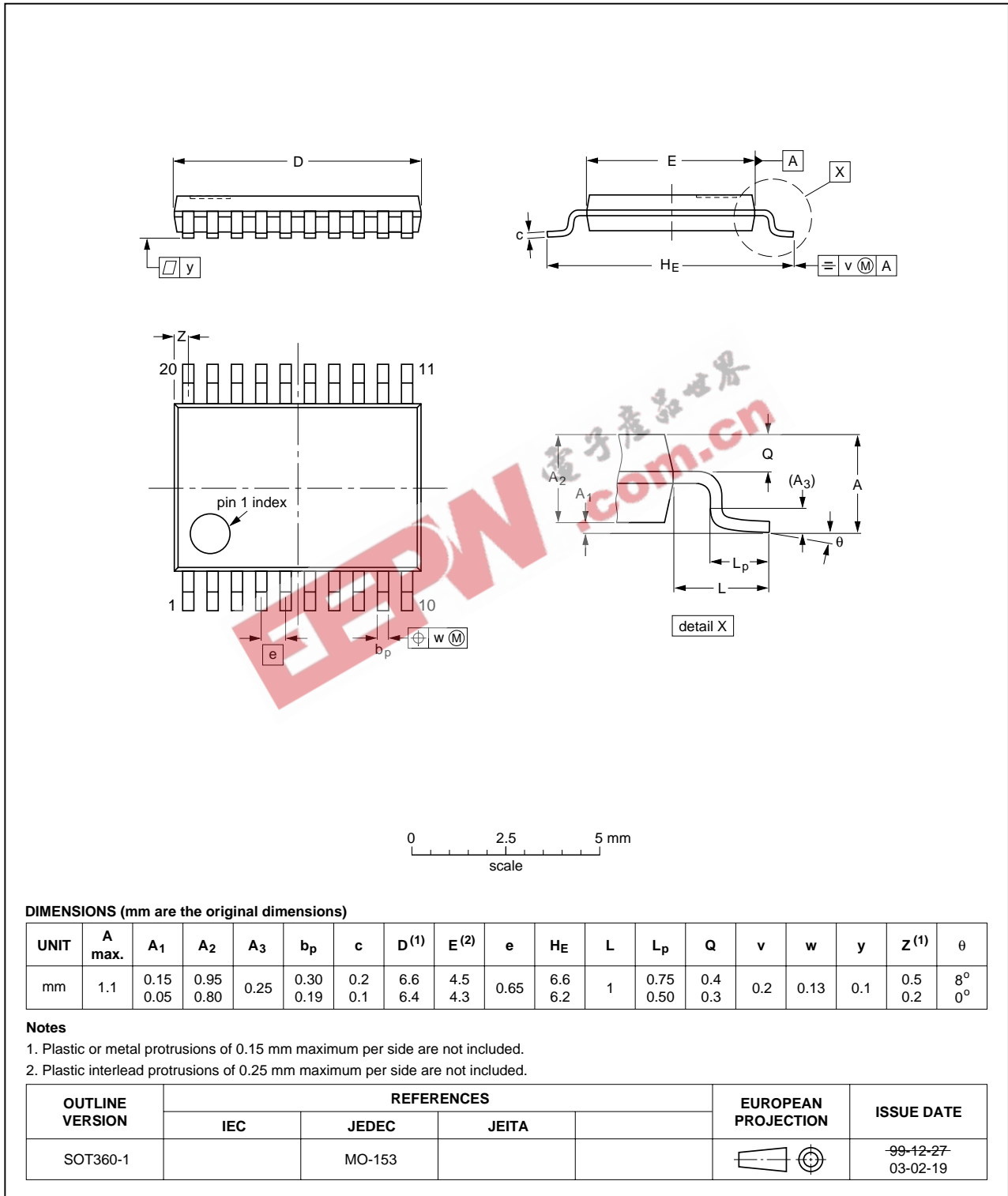


Fig 9. Package outline SOT360-1 (TSSOP20)

DHVQFN20: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body 2.5 x 4.5 x 0.85 mm

SOT764-1

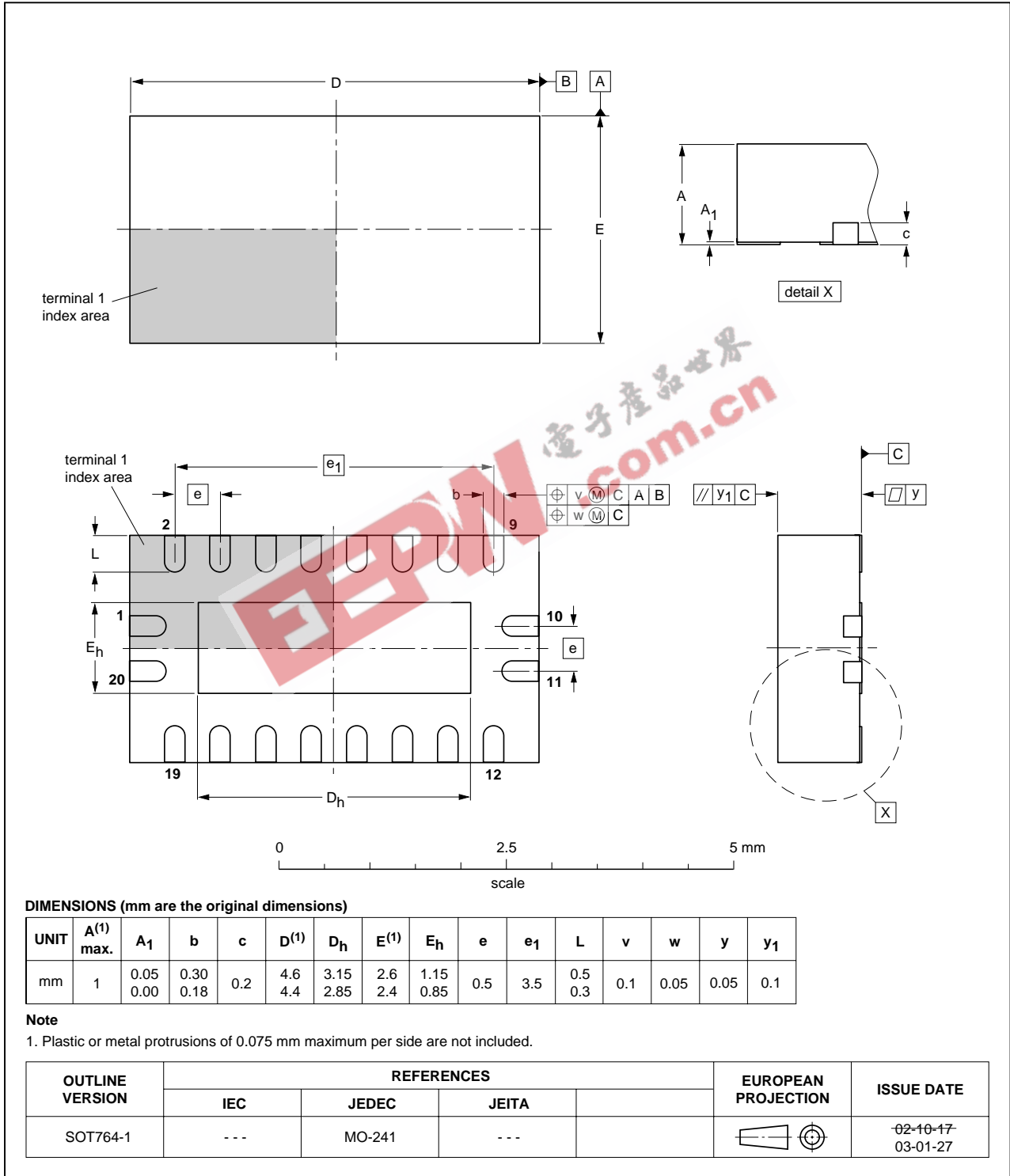


Fig 10. Package outline SOT764-1 (DHVQFN20)

## 13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

## 14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74ALVC245_2	20080107	Product data sheet		74ALVC245_1
Modifications:		<ul style="list-style-type: none"> <li>The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> <li><a href="#">Section 3</a>: DHVQFN20 package added.</li> <li><a href="#">Section 7</a>: derating values added for DHVQFN20 package.</li> <li><a href="#">Section 12</a>: outline drawing added for DHVQFN20 package.</li> </ul>		
74ALVC245_1	20030710	Product specification	-	-

## 15. Legal information

### 15.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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